



Transient Voltage Suppressors for ESD protection

DESCRIPTION

The KESD3E5C is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

This device has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

ORDERING INFORMATION

→ Package: SOD-323→ Material: Halogen free→ Packing: Tape & Reel

♦ Quantity per reel: 3,000pcs

FEATURES

♦IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)

♦IEC61000-4-4 (EFT) 40A (5/50ns)

♦Peak power dissipation: 200W (8/20µs)

♦Protects one directional I/O line

Low clamping voltageWorking voltages : 5VLow leakage current

MACHANICAL DATA

♦SOD-323 package

♦ Terminals: Gold plated, solderable per MIL-STD-750, method 2026

♦Packaging: Tape and Reel

♦Reel size: 7 inch

APPLICATIONS

♦ High Speed Line: USB1.0/2.0, VGA, DVI, SDI,

♦ Serial and Parallel Ports

♦Notebooks, Desktops, Servers

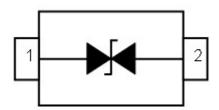
♦Projection TV

♦ Cellular handsets and accessories

♦Portable instrumentation

♦Peripherals

PIN CONFIGURATION



PACKAGE OUTLINE

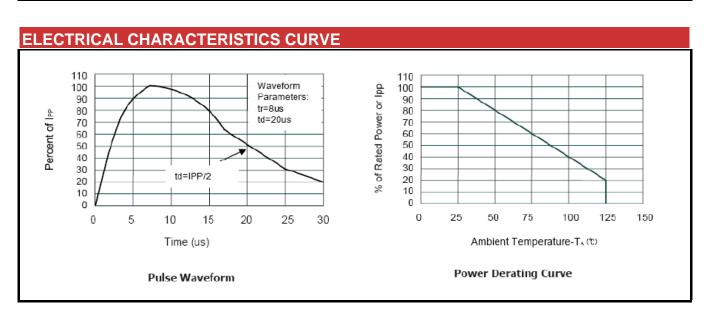




KESD3E5C

ABSOLUTE MAXIMUM RATING						
Symbol	Parameter	Value	Units			
V _{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±15 ±8	kV			
P _{PP}	Peak Pulse Power (8/20µs)	100	W			
T _{OPT}	Operating Temperature	-40~150	°C			
T _{STG}	Storage Temperature	-40~150	°C			

ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V_{RWM}	Reverse Working Voltage				5.0	V		
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	5.6		7.8	V		
I _R	Reverse Leakage Current	V _{RWM} = 5V			1.0	μΑ		
V _C	Clamping Voltage	$I_{PP} = 5A, t_p = 8/20 \mu s$			11.6	V		
V _C	Clamping Voltage	$I_{PPmax} = 8A$, $t_p = 8/20\mu s$			16.0	V		
С	Junction Capacitance	V _R = 0V, f = 1MHz		10	15	pF		



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